

Femtosecond laser 3D micro-structuration in silica-based glasses

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ICMMO/EPCES/MAP

Advanced Materials for Photonics

Femtosecond laser 3D processing in silica

Part 1

Motivations

Why silica glass ?

Owing to both excellent physical and chemical properties such as:

- Optical transparency over a wide range of wavelengths (UV-NIR)
- Stable properties over time and at high temperature
- High damage threshold

Silica-based (SiO_2) glasses prove to be key materials of today's rapidly expanding photonics application areas such as:

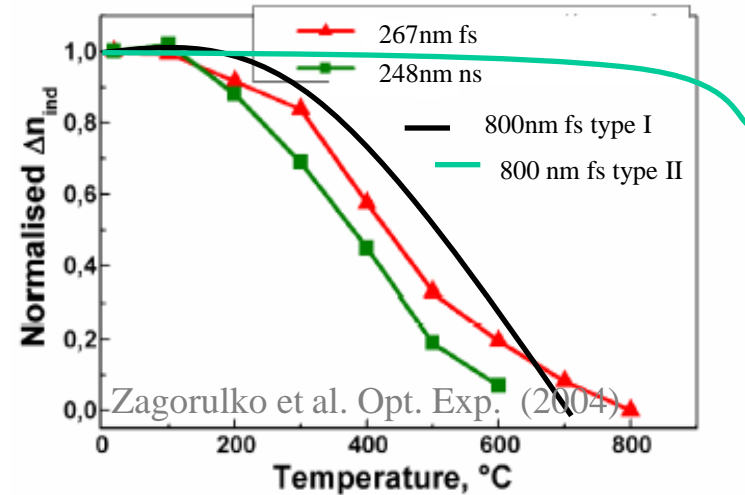
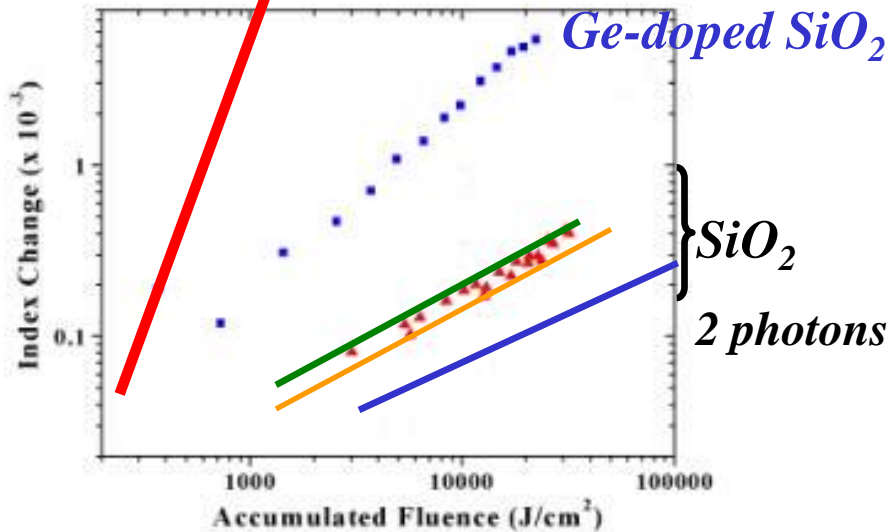
- Electronics
- Sensor technologies
- Optical communications (optical fibers)
- Material processing (e.g. Fiber Bragg Gratings, optics)

e.g. Over the last 20 years UV-induced Δn profiling in SiO_2 based glasses was widely used for production of in-fibre/waveguide Bragg grating-based (BG) devices...

Pure silica glasses exhibit poor photosensitivity to UV-laser light !!!

Whereas using IR-fs laser Δn up to $2.2 \cdot 10^{-2}$ Eaton et al. JNCS. 2010

IR-fs (6 photons) F. Quéré et al., EPL 2001



ns-193nm: $\Delta n \approx 3 \cdot 10^{-4}$ for 140 kJ/cm^2
Albert et al. Opt. Lett. 2001

ns-157-nm : $\Delta n \approx 4 \cdot 10^{-4}$ for 30 kJ/cm^2 Herman et al. Riken Rev. 2001

ps-213nm or fs-264nm; $\Delta n = 4 \cdot 10^{-4}$ Pissadakis et al. Opt. Exp 2005

UV: Similar stability from ns to fs

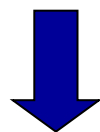
But IR-fs type II are more stable !

Bricchi et al. APL 2006

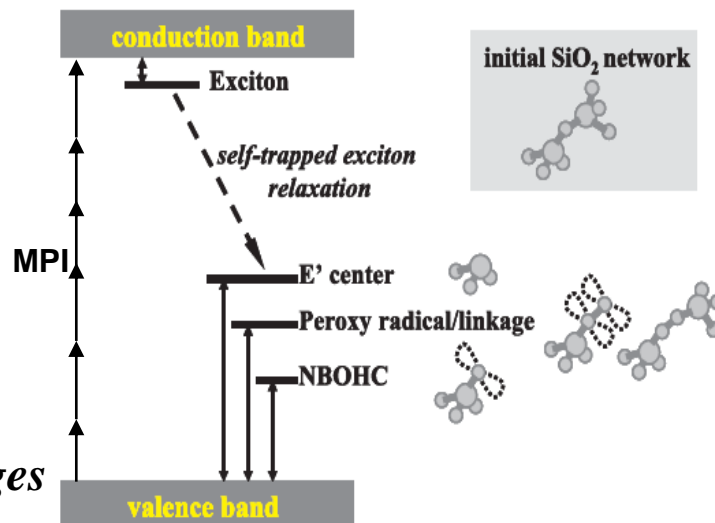
Exposing SiO₂ to pulsed ($\approx 50-500$ fs) laser power densities ($\approx 1-100$ TW/cm²)



Investigation of *multiphoton reaction-induced* in glasses that do not linearly absorb efficiently at the laser wavelength



Various permanent changes in macroscopic physical properties such as: *ablation, 3D photo-structural changes and refractive index changes (i.e. Photosensitivity)*



Mao et al. Appl. Phys. A 79 (2004)

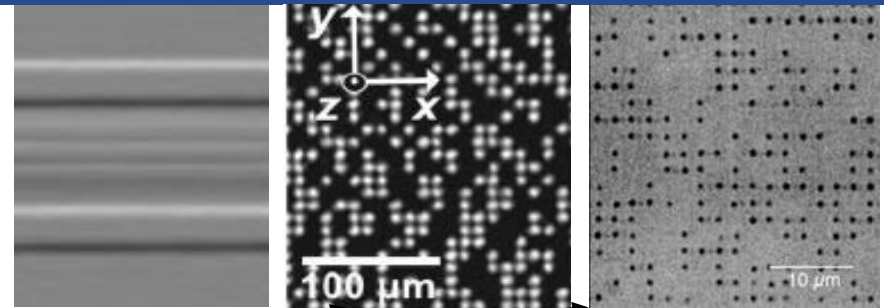
F. Quéré et al., EPL (2001)

P. Martin et al., PRB 55 (1997)

Today talk about permanent changes !

But we are strongly interested by transient processes e.g. photo-ionization processes, plasma density, STE, thermal effects... since they are at the roots of the permanent structural changes

3D localization !!! Due to NL-effects and ultrashort pulse duration



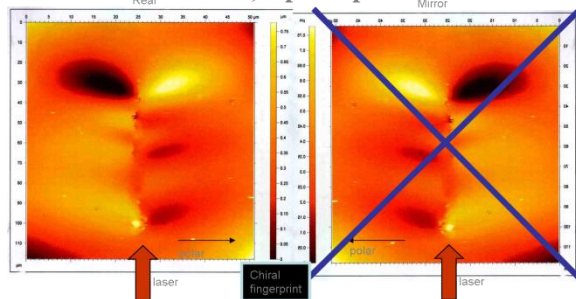
Main optical properties:

- Refractive index (isotropic, anisotropic, voids)
- Absorption (e.g. linear and circular dichroism especially in the VUV-UV)
- Non-linear optical properties (metallic nanoparticles, nano/micro-crystals)

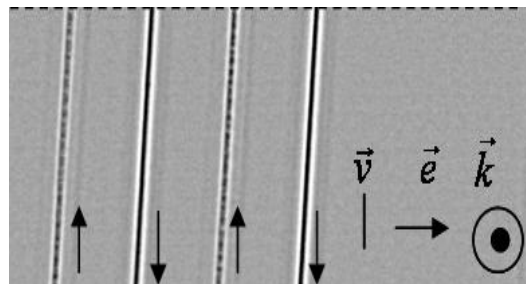
Hence, this renders fs-processing attractive for material laser 3D processing !!!

“Amazing” structures: chiral mechanical structures, orientational dependent writing, “self-organized” nanogratings

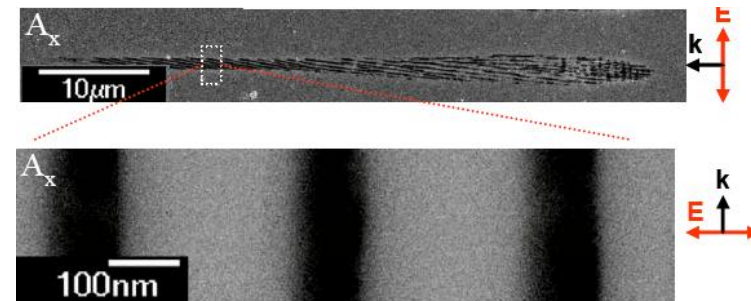
Poumellec et. al. Opt. Express 2003 & 2008



Kazansky et al. APL 2006



Shimotsuma et al. Phys. Rev. L 91 (2003)
Kazansky, et al. Appl. Phys. Lett. 90 (2007) 151120.



Femtosecond laser 3D processing in silica-based glasses

Part 2

Results

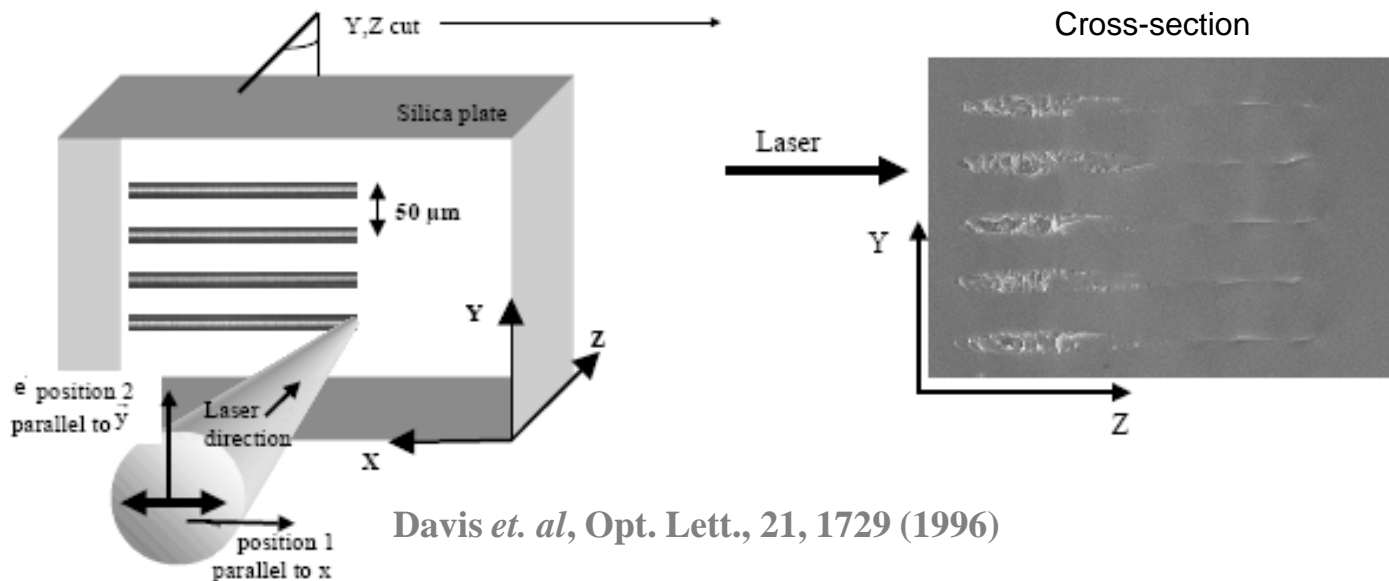
Typical irradiation parameters in amorphous SiO₂

$\lambda = 400-1500\text{nm}$ (typ. 800 ou 1030), *i.e. the electronic photo-excitation is finished before the transfer to the lattice (temperature increase)*
 Pulse duration typ. 100-300 fs

Pulse energy: 0.01-2 μJ (10^{12-14}W/cm^2) *i.e. energy deposited by 1 pulse in the focal volume \cong formation energy of the silica oxide glass*

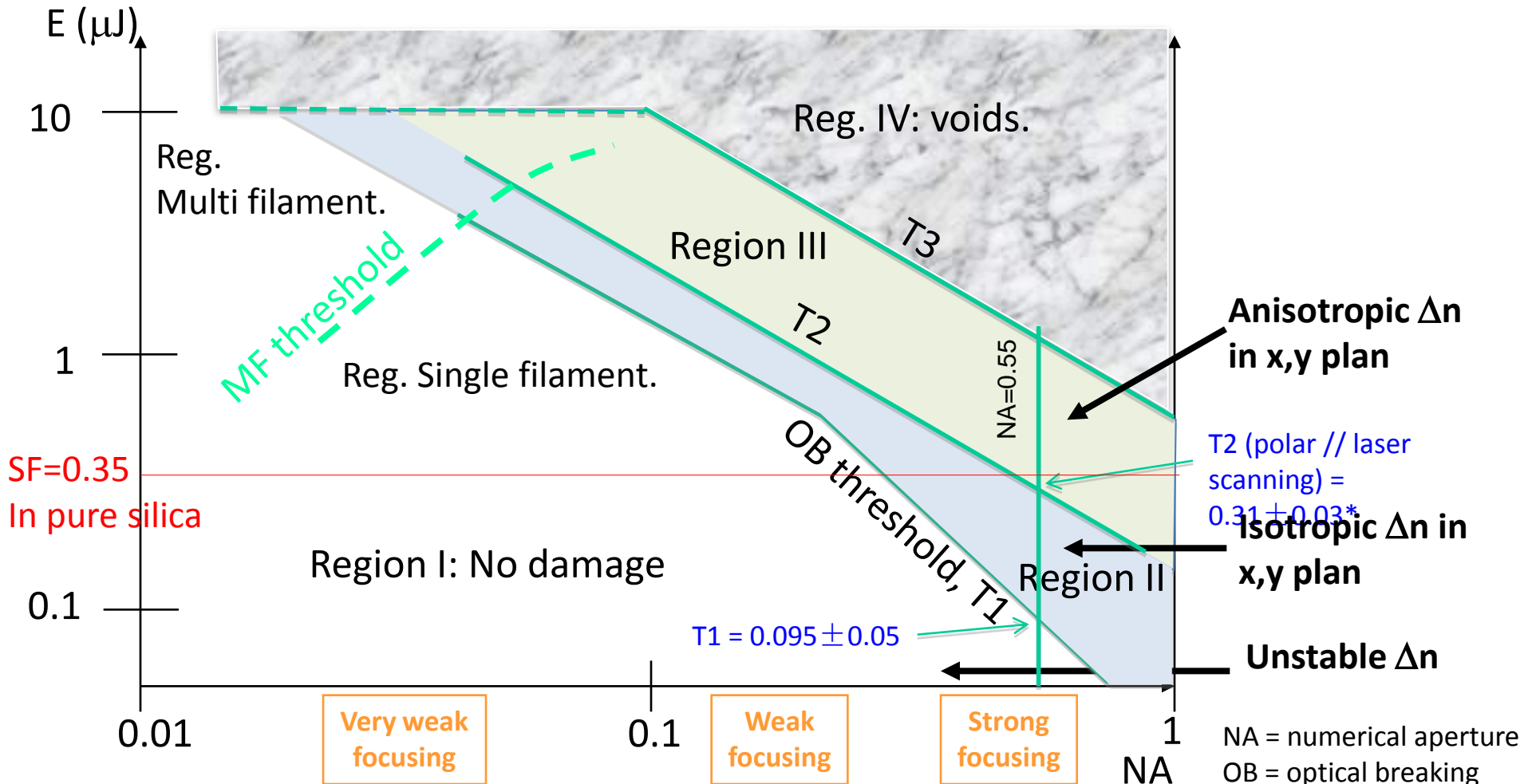
“Tight” focusing in volume NA = 0.1-1.4 (typ. 0.5) *i.e. waist $\cong 1.5 \mu\text{m}$*

Repetition rate: up to 80MHz (typ. 100’s kHz) *Heat diffusion in silica = 1 μs i.e. no accumulation below 1MHz*



Davis *et. al*, Opt. Lett., 21, 1729 (1996)

SiO₂, 800 nm, 160 fs, 100 kHz, 100 μm/s, conf //

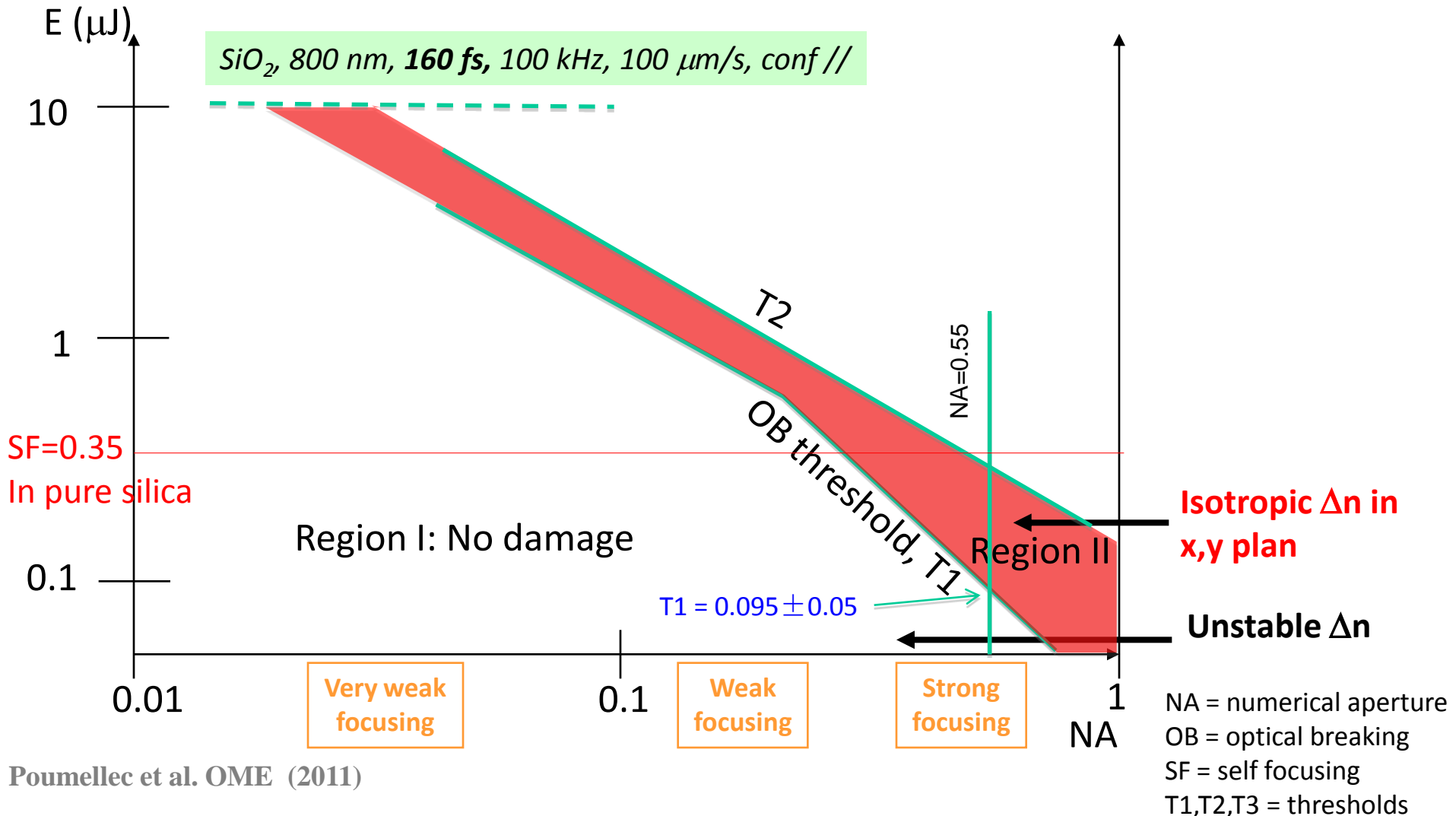


Fs laser processing in silica-based glasses

Region II i.e. above T1 and below T2

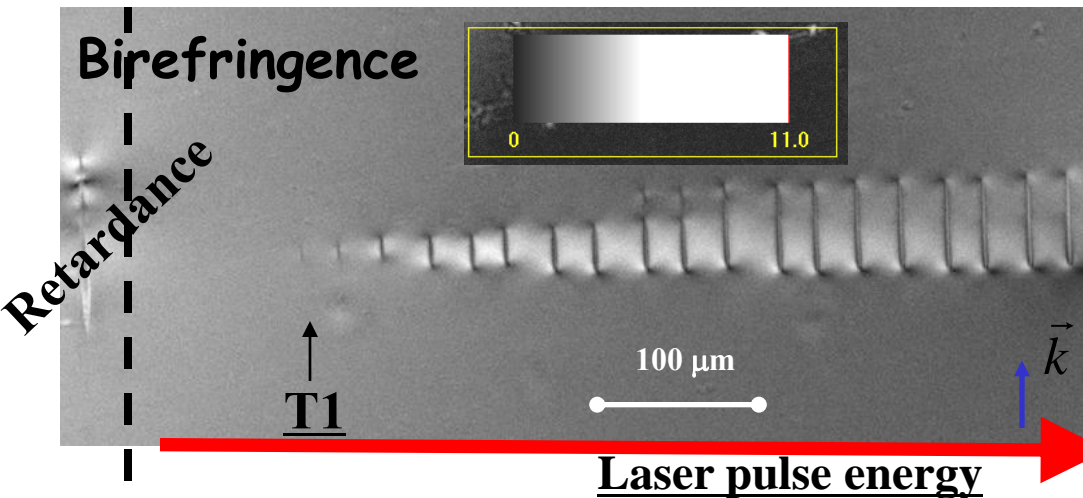
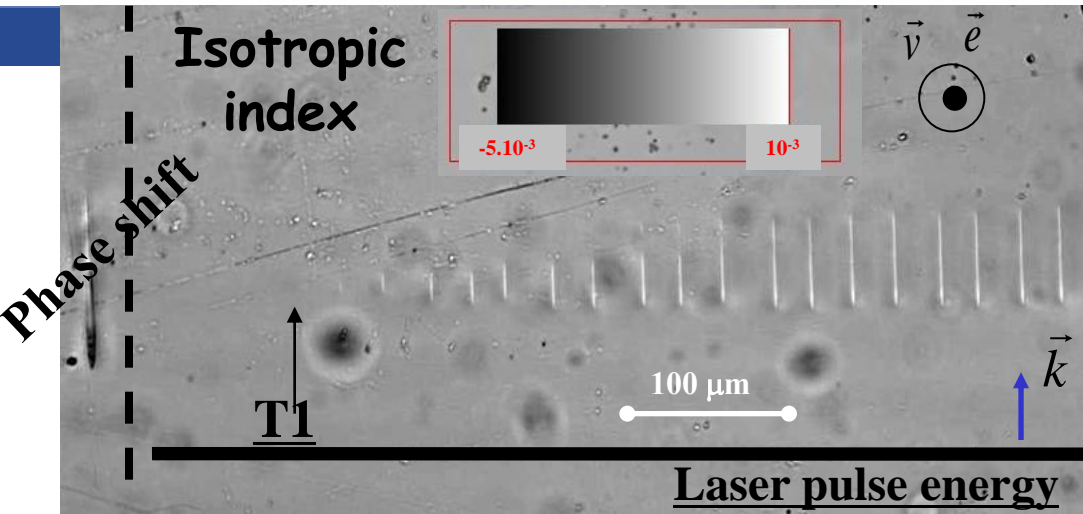


The first energy threshold (T1) is the minimum energy requested for observing a change in the material (it depends slightly on the number of pulses).



SiO₂

Laser track cross section

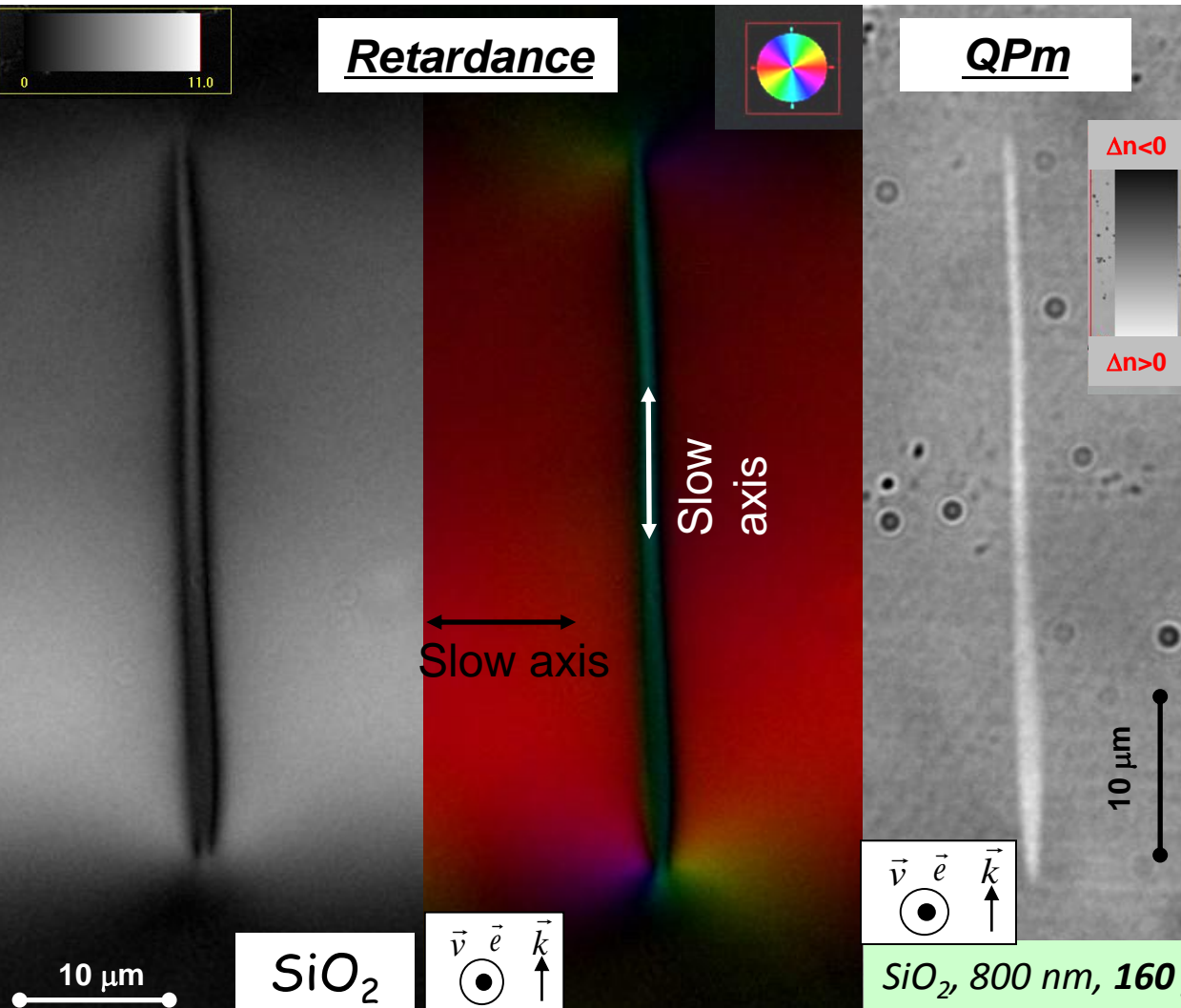


SiO₂, 800 nm, 160 fs, 100 kHz, 100 $\mu\text{m/s}$, 0.05-0.4 μJ , conf //

Laser track cross section

Uniform Δn along the laser track i.e. $\Delta n > 0$ in the laser tracks (\approx typ. 10^{-3})

Lancry et al. BGPP conf (2010)



Δn origins are similar to UV laser irradiation i.e.

- **Permanent densification**

Chan et al. Appl. Phys. A 76 (2003) 367

Hosono et al. NIM PRB 191 (2002) 89

- **Related stress field**

Erraji-Chahid et al. BGPP conf (2010)

Poumellec et al. Opt. Express (2008)

- **Defects centers**

Hosono et al. NIM PRB 191 (2002) 89

Sun et al. J. Phys. Chem. B 104 (2000) 3450

Lancry et al. OME (2012, In proof)

SiO_2 , 800 nm, 160 fs, 100 kHz, 100 $\mu\text{m/s}$, 0.2 μJ , conf //

Δn origin: T_f local increases and related specific volume change

Energy « deposition », large increase in local temperature (after a few 10's ps), thermal diffusion and temperature decreases in a time δt that depends on W and on material properties

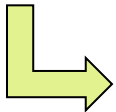
If δt is larger than the time required for the glass structure to change (the relaxation time η/G , $\eta(T)$ the glass viscosity, $G(T)$ the glass shear modulus), the modification is permanent i.e. the average disorder of the glass or the fictive temperature is changed.

$$h(T_c) / G(T_c) = dt(T_c)$$

SiO₂, 800 nm, 160 fs, 100 kHz, 100 μm/s, 0.2 μJ, conf //

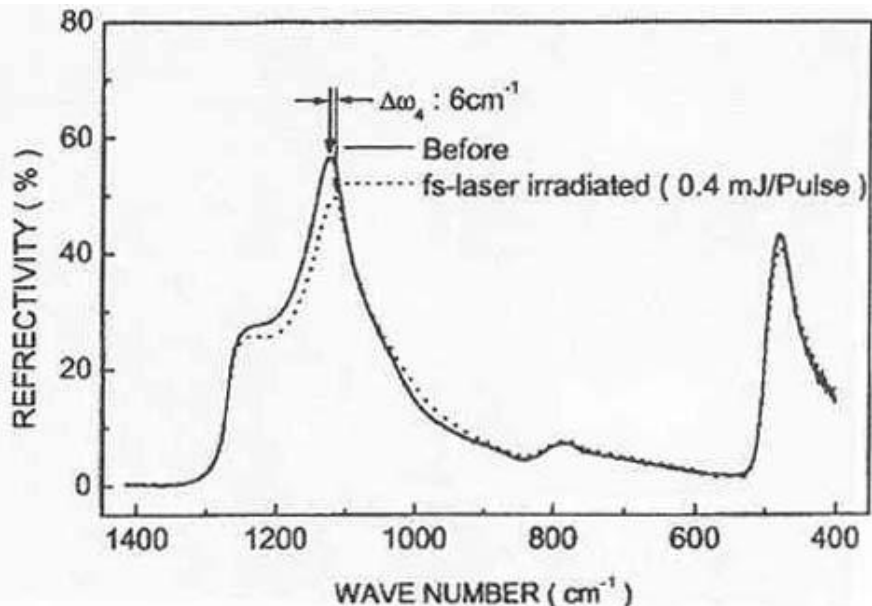
T_c is the new fictive temperature

In most glasses, the increase of fictive temperature corresponds to the decrease of density and thus to a decrease of average index. But in silica, it is the reverse (anomalous behaviour)



Waveguide / gratings fabrication

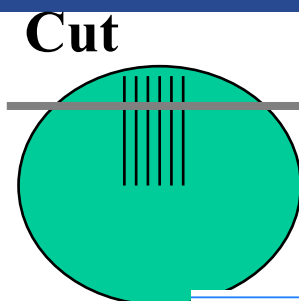
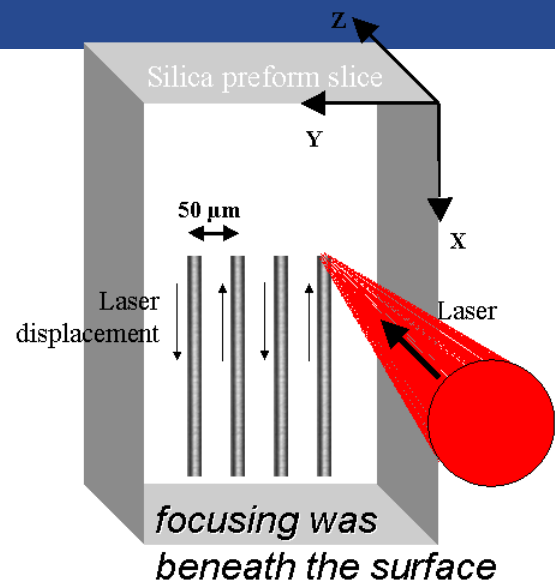
e.g. T_f increases of 500° C leads to $\Delta n = +10^{-3}$ [Bru70, She04]



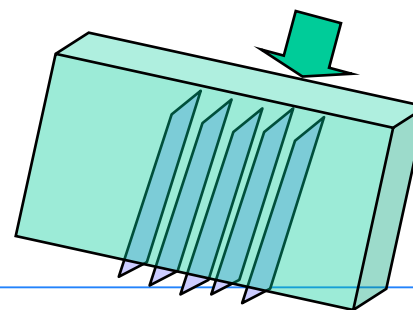
Chan et al. Appl. Phys. A 76 (2003) 367

Hosono et al. NIM PRB 191 (2002) 89

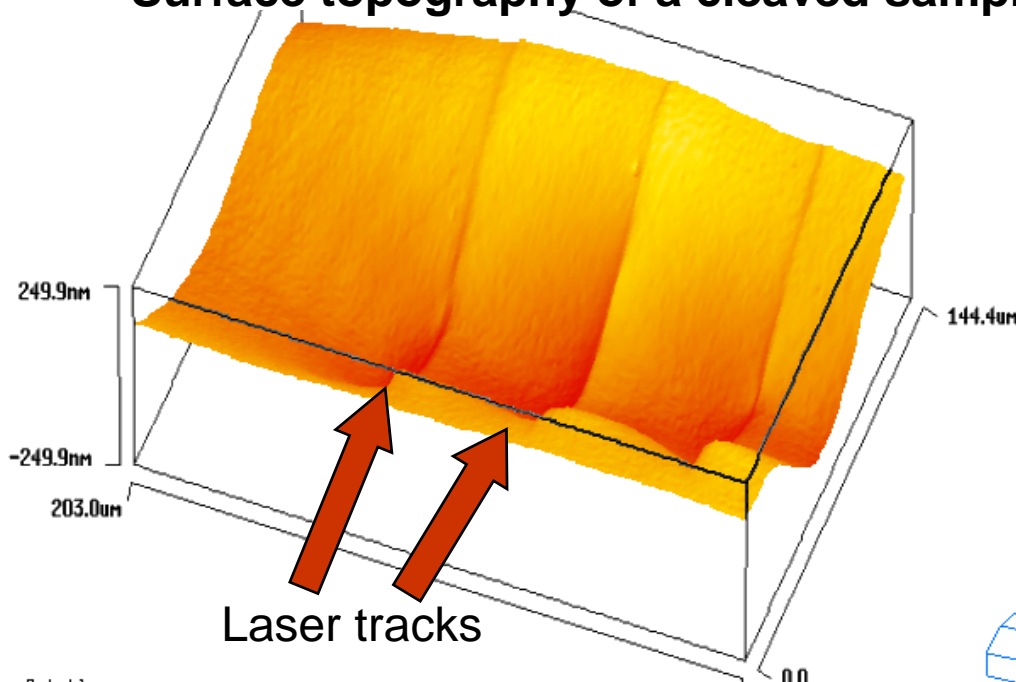
Δn origin : permanent densification and related stress field



Phase shift interferometry
or AFM



Surface topography of a cleaved sample



Ti :Sa laser at 800 nm, 160 fs,
0.35-1.5 μJ , 100 kHz, 0.5 NA,
Pure silica

• **Related stress field relaxation**

Erraji-Chahid et al. BGPP conf (2010)

Poumellec et al. Opt. Express (2008)

On a une variation de volume spécifique localisée i.e. une déformation isotrope libre de contrainte qui engendre un champ de contrainte.

$$r(\vec{r}) \supset e^p(\vec{r}) \supset s(\vec{r}) \quad \text{ou} \quad e^e(\vec{r})$$

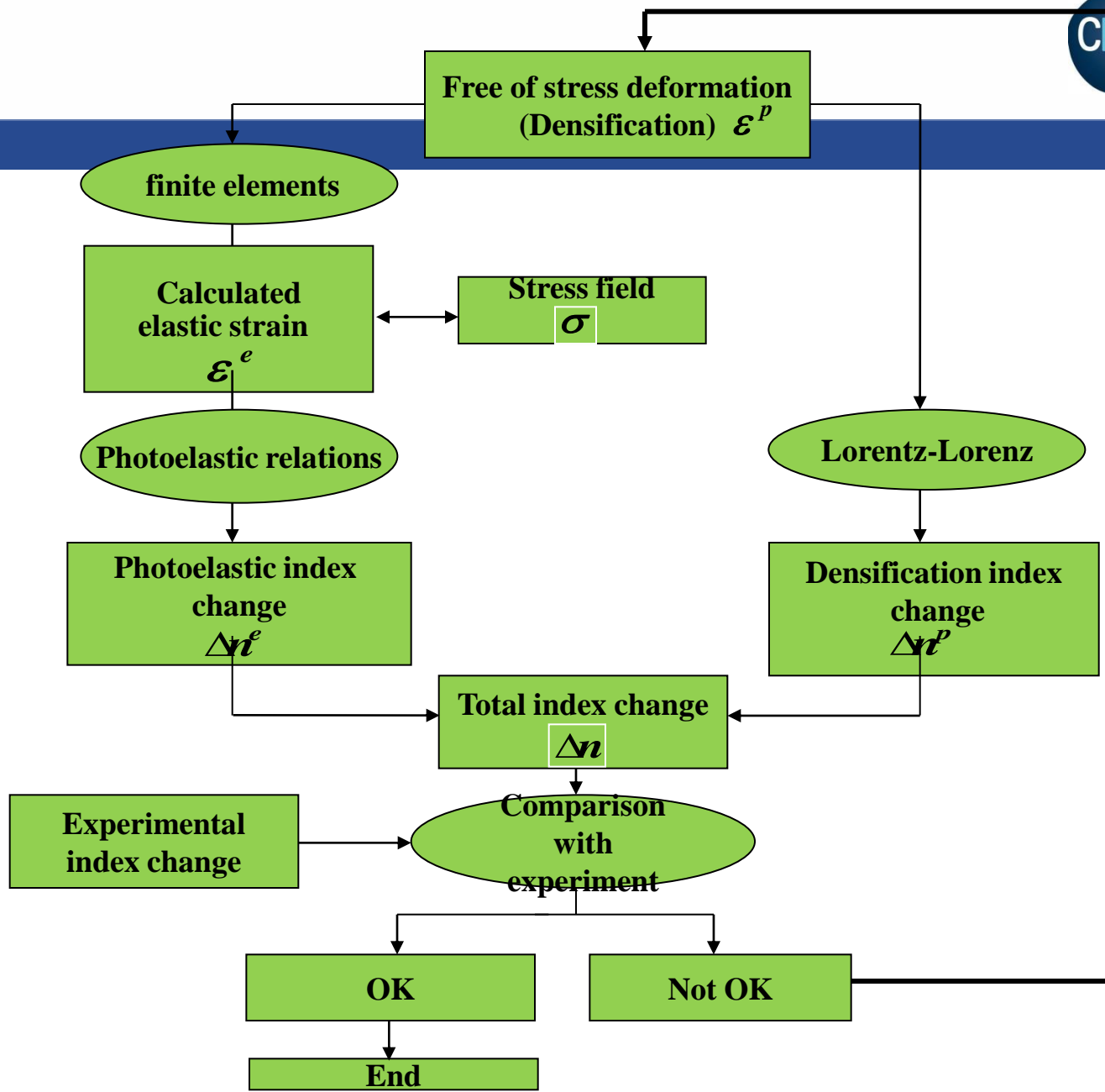
et une variation d'indice qui provient du champ de contrainte

$$\Delta n_{ii}^p = - \frac{(n^2 - 1)(n^2 + 2)}{2n} (1 - W) e^p$$

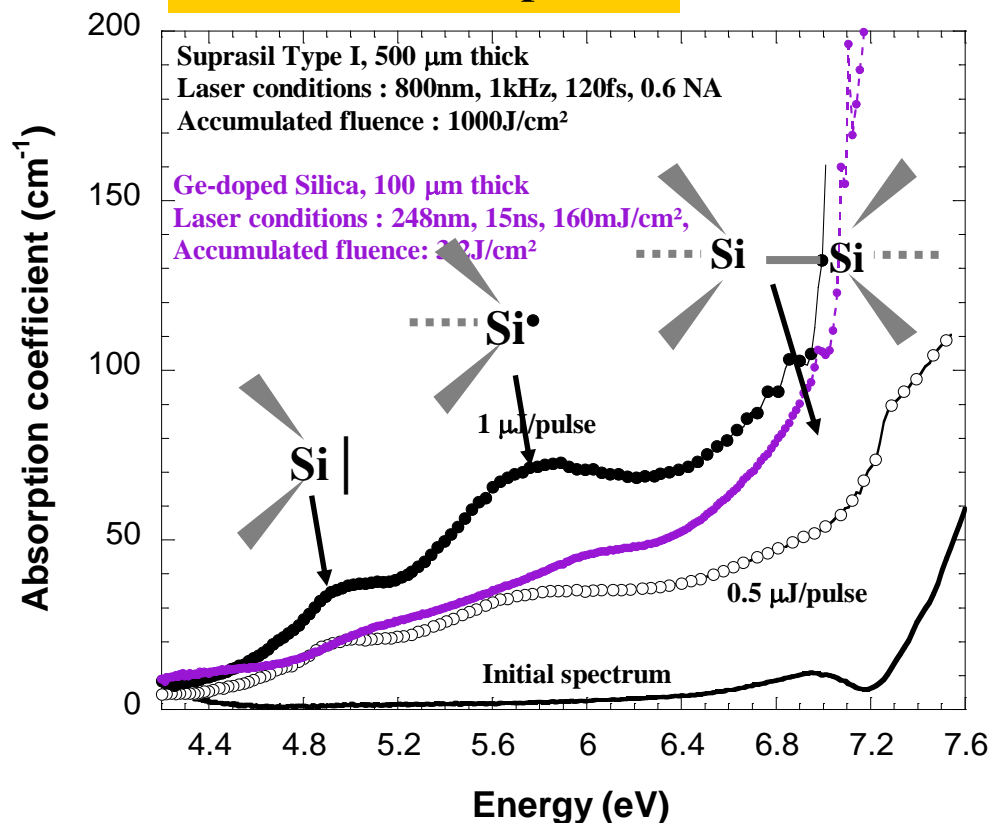
On a une variation de volume spécifique localisée qui engendre une variation d'indice (Lorentz-Lorenz)

Pb: calculer le champ de contrainte à partir de la déformation libre de contrainte, mais quel est le bon champ de déformation?

$$\left\{ \begin{array}{l} \Delta n_{xx}^e = - \frac{n^3}{2} (p_{11} \varepsilon_{xx}^e + p_{12} \varepsilon_{yy}^e + p_{12} \varepsilon_{zz}^e) \\ \Delta n_{yy}^e = - \frac{n^3}{2} (p_{12} \varepsilon_{xx}^e + p_{11} \varepsilon_{yy}^e + p_{12} \varepsilon_{zz}^e) \\ \Delta n_{zz}^e = - \frac{n^3}{2} (p_{12} \varepsilon_{xx}^e + p_{12} \varepsilon_{yy}^e + p_{11} \varepsilon_{zz}^e) \\ \Delta n_{xy}^e = - \frac{n^3}{2} (p_{11} - p_{12}) \varepsilon_{xy}^e \\ \Delta n_{yz}^e = - \frac{n^3}{2} (p_{11} - p_{12}) \varepsilon_{yz}^e \\ \Delta n_{xz}^e = - \frac{n^3}{2} (p_{11} - p_{12}) \varepsilon_{xz}^e \end{array} \right.$$



UV-VUV absorption

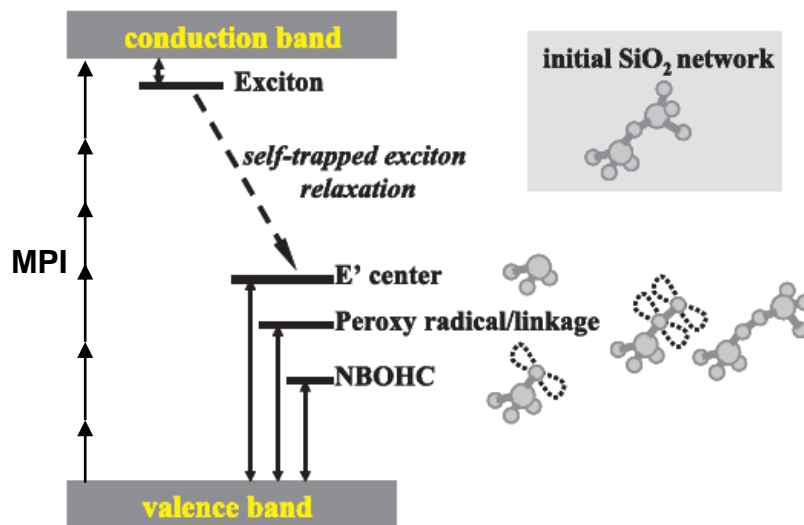


Defects centers

Hosono et al. NIM PRB 191 (2002) 89

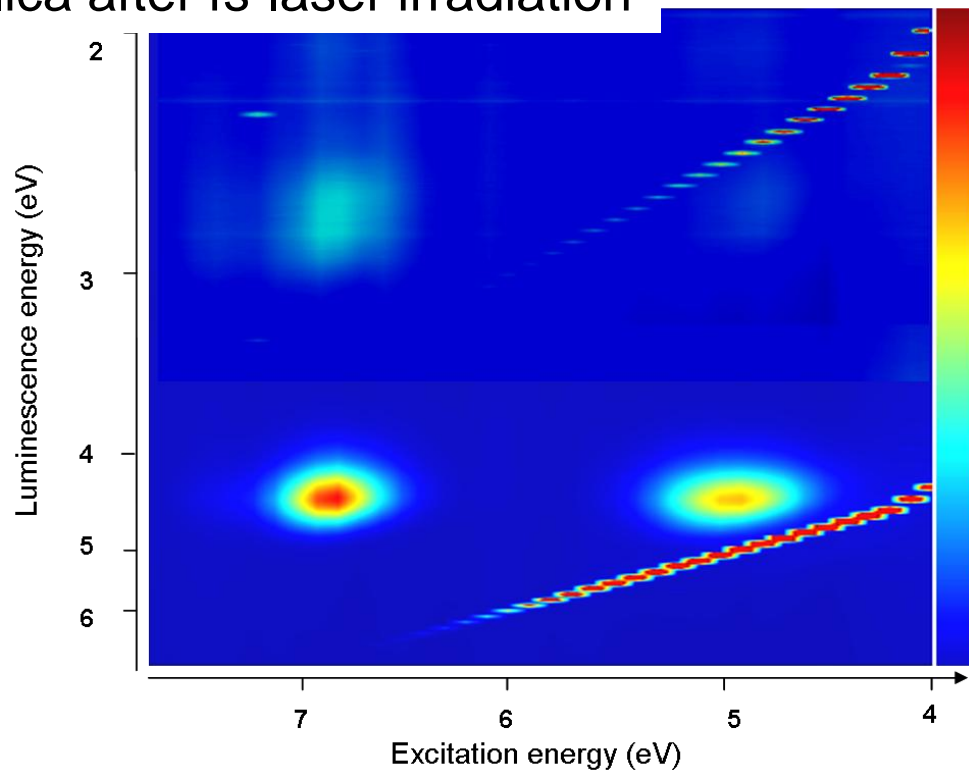
Sun et al. J. Phys. Chem. B 104 (2000) 3450

Lancry et al. SiO₂ conf (2010) , Accepted in Optical Material Express (2012)



UV-VUV excitation spectroscopy

Pure silica after fs-laser irradiation



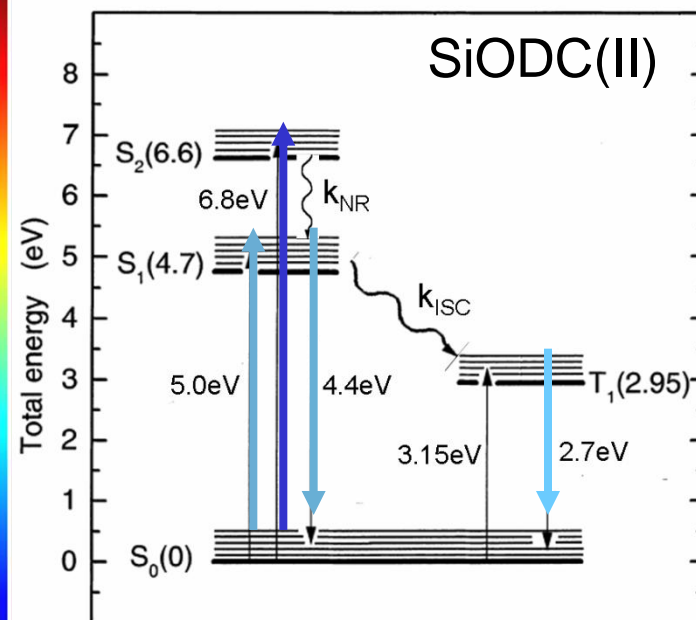
T_1

S_1

S_0

S_2

S_1

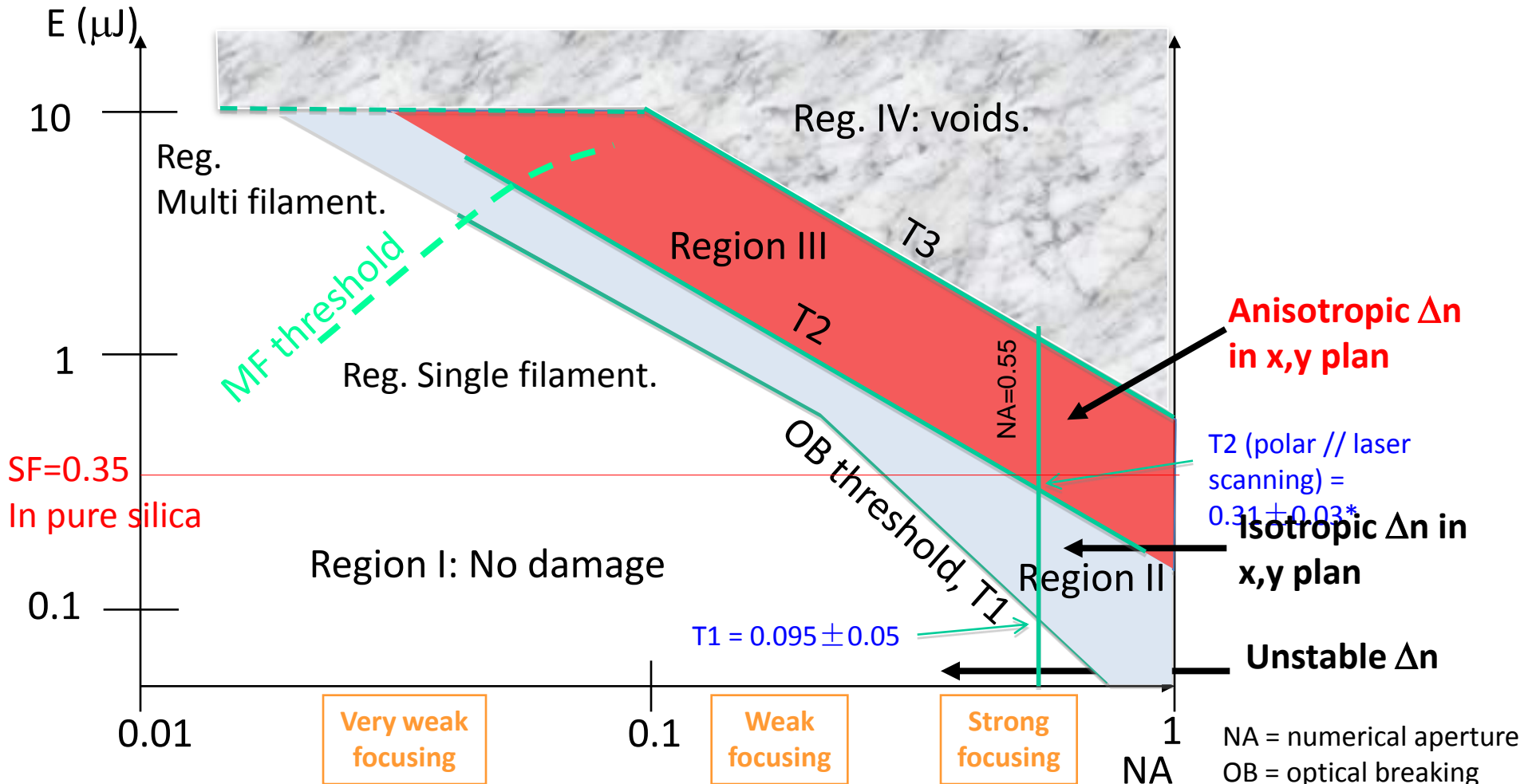


Optical transition scheme in Si-related oxygen deficient center SiODC(II). After L.Skuja, JNCS 239, (1998), 16-48.

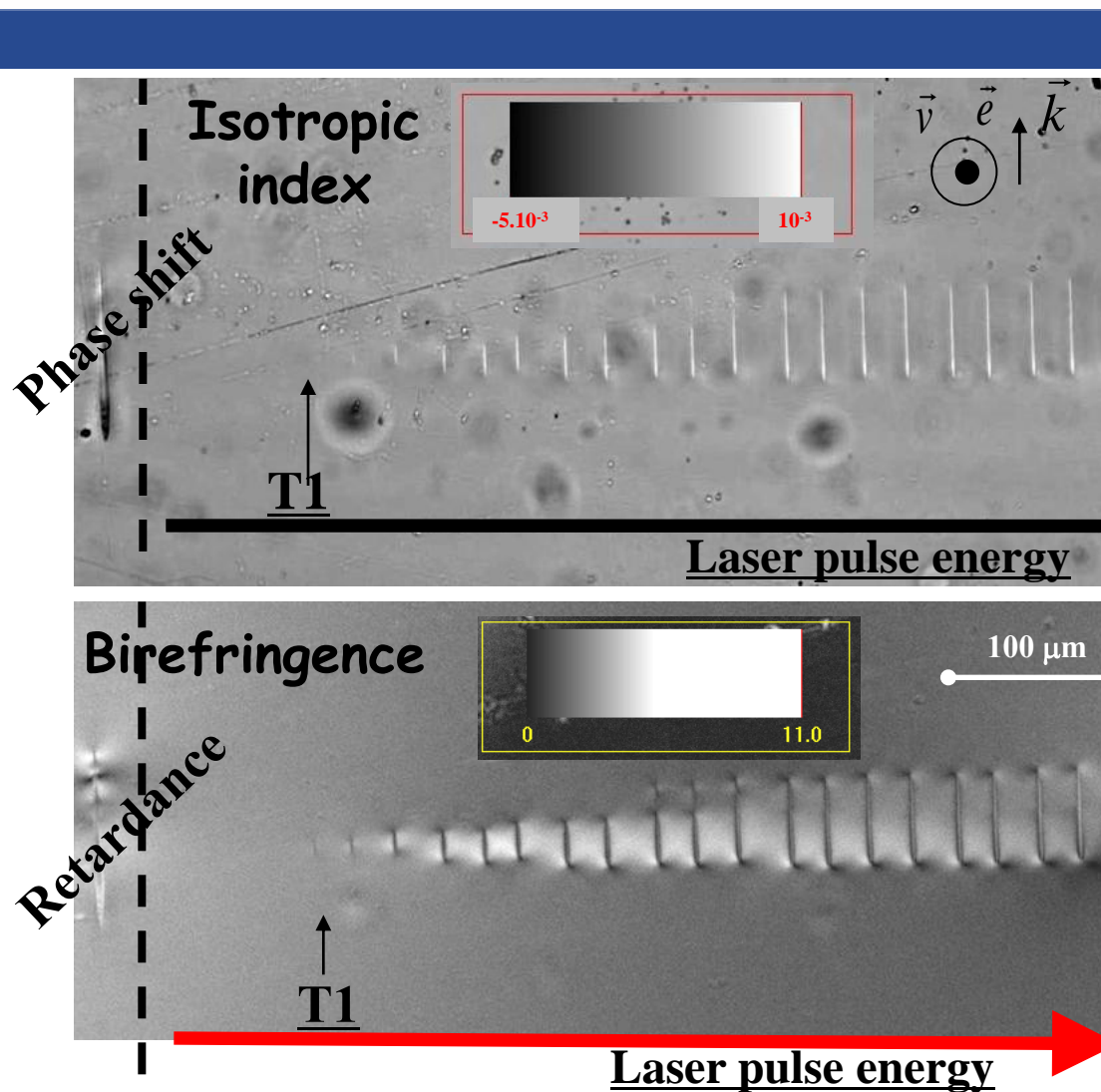
Lancry et al. OME (2012, in Proof)
Poumellec et al. SUM (2011)

800nm, 1kHz, 120fs, 0.6NA, 0.5 μ /pulse, 10 μ m/s, linear polarization

SiO₂, 800 nm, 160 fs, 100 kHz, 100 μm/s, conf //

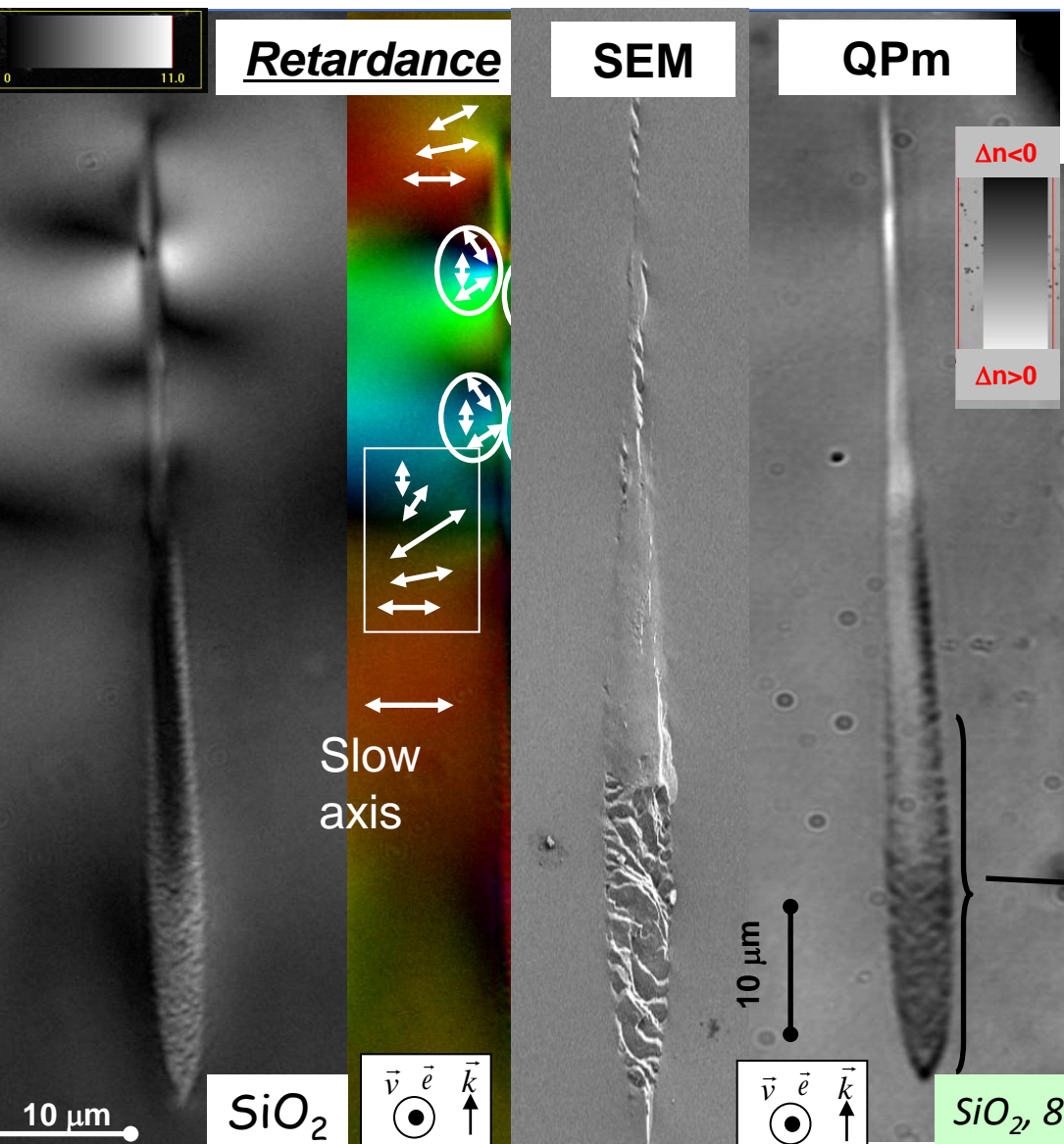


Laser track cross section



SiO_2 , 800 nm, 160 fs, 100 kHz, 100 $\mu m/s$, 0.05-1.2 μJ , conf //

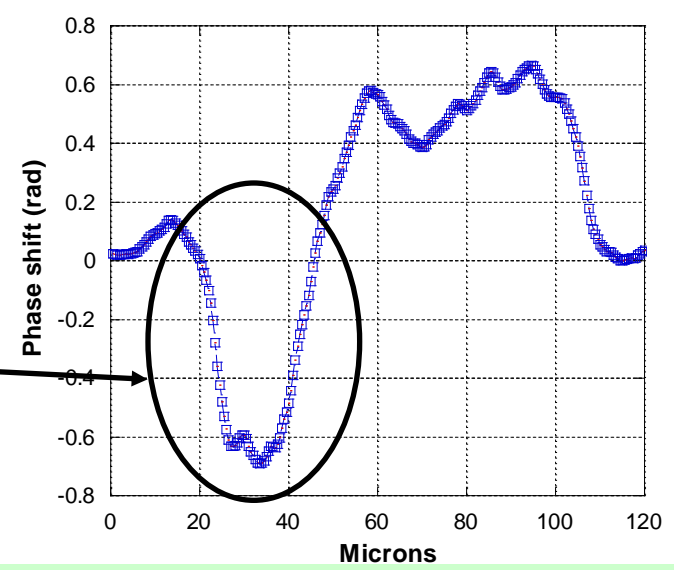
Laser track cross section



Strong birefringence (up to $1.2 \cdot 10^{-2}$ or 250 ± 3 nm retardance in one layer)
 + "residual" stress birefringence
 Lancry et al. AIOM conf (2009)

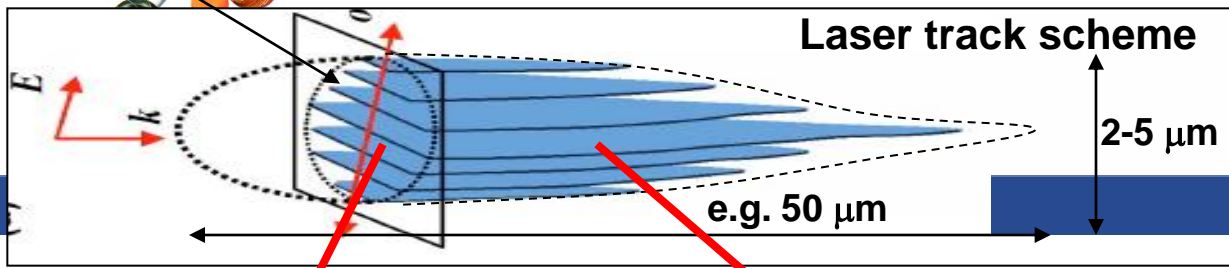
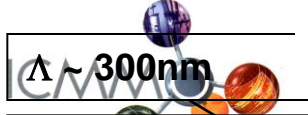
Non-uniform Δn :

- $\Delta n < 0$ ($\approx -5 \cdot 10^{-3}$) in the head
- $\Delta n > 0$ in the tail (**up to $2.2 \cdot 10^{-2}$**)



SiO₂, 800 nm, 160 fs, 100 kHz, 100 $\mu\text{m/s}$, 1 μJ , conf //

Birefringence and negative index changes origin



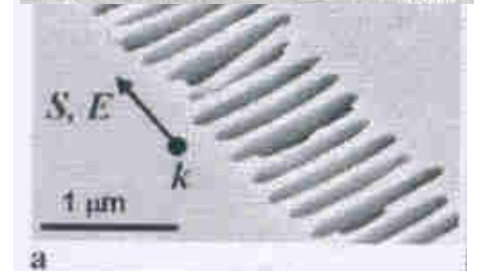
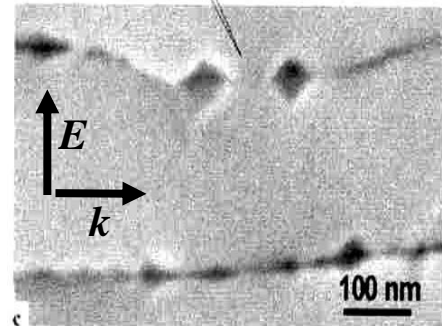
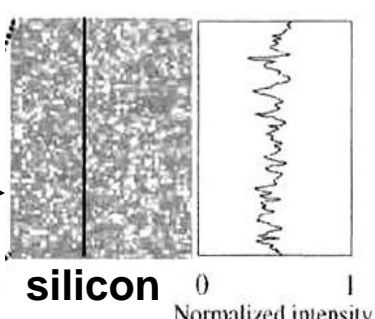
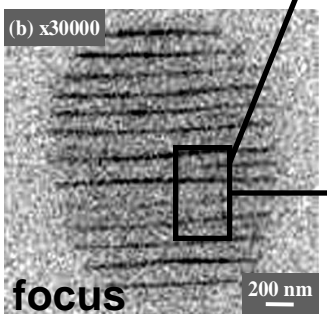
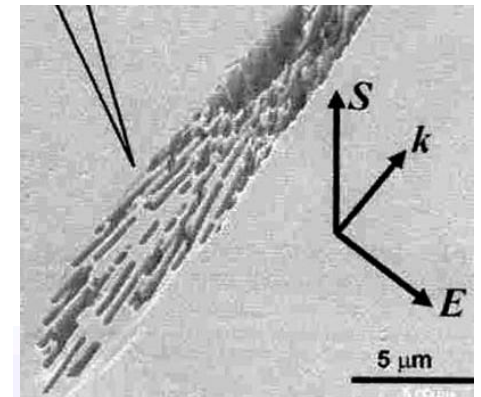
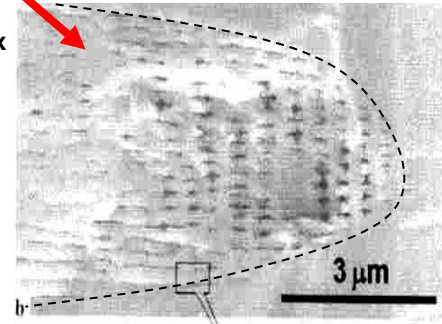
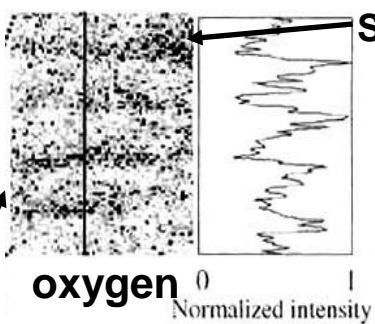
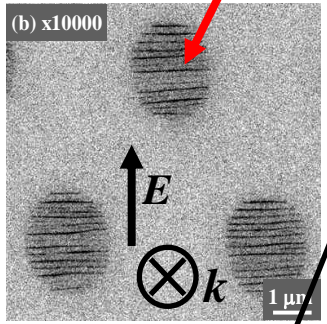
Nanogratings at the roots of form birefringence

Backscattered e⁻

Auger photoemission

Cut, polish, SEM

HF Etching, SEM



Shimotsuma et al. Phys. Rev. B 91 (2003)

Hnatovsky Appl. Phys. Lett. 87 (2005)

Hnatovsky Appl. Phys. A 84 (2006)

800nm, 150fs, 1-3 μJ/pulse, 200 kHz, NA=0.95

800nm, 150fs, 0.3 μJ/pulse, 100 kHz, NA=0.65

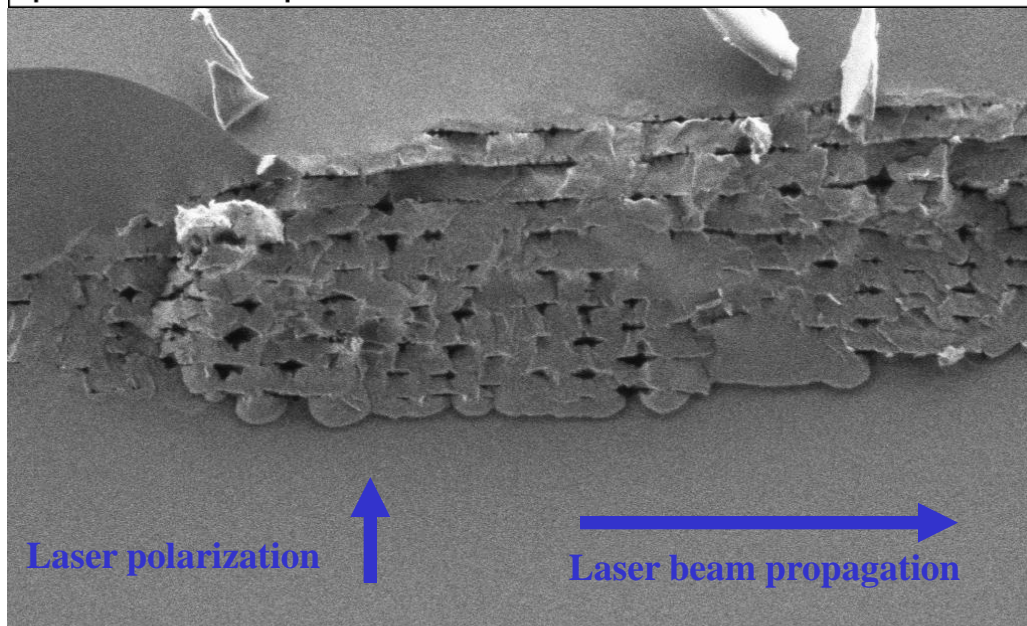
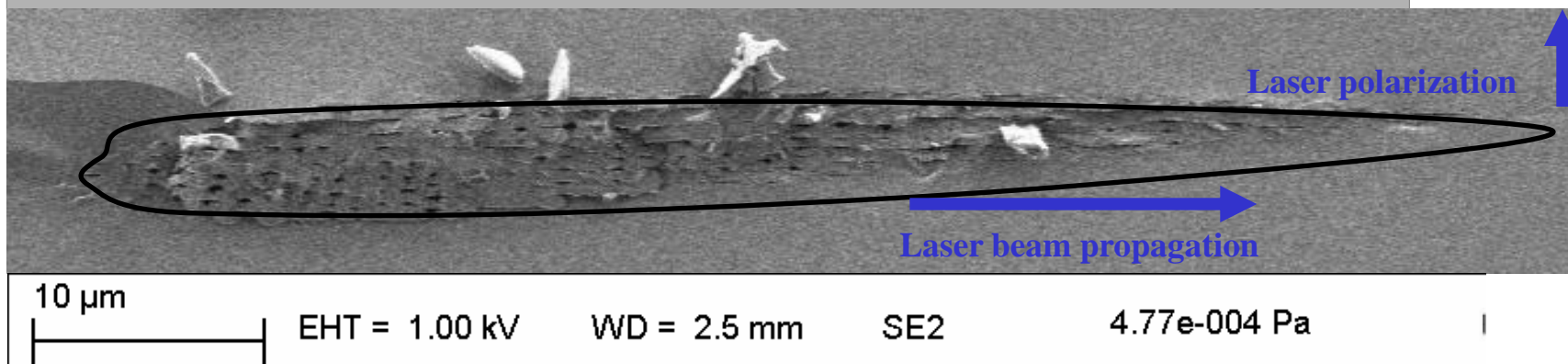
Oxygen segregation ?

Nanocracks ?

weakening of the structure

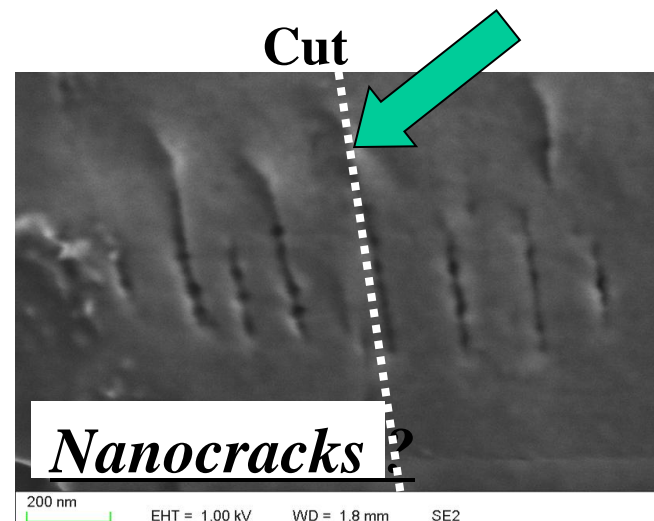
So what is the intimate structure of these nanoplanes and how to probe it ?

SEM images of a whole laser track written in perpendicular configuration.



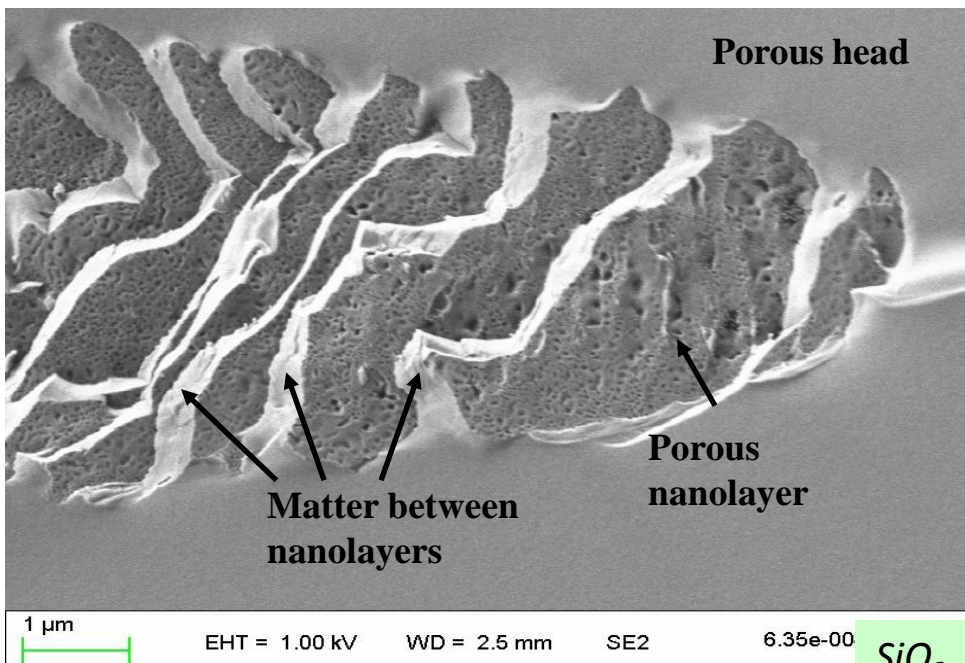
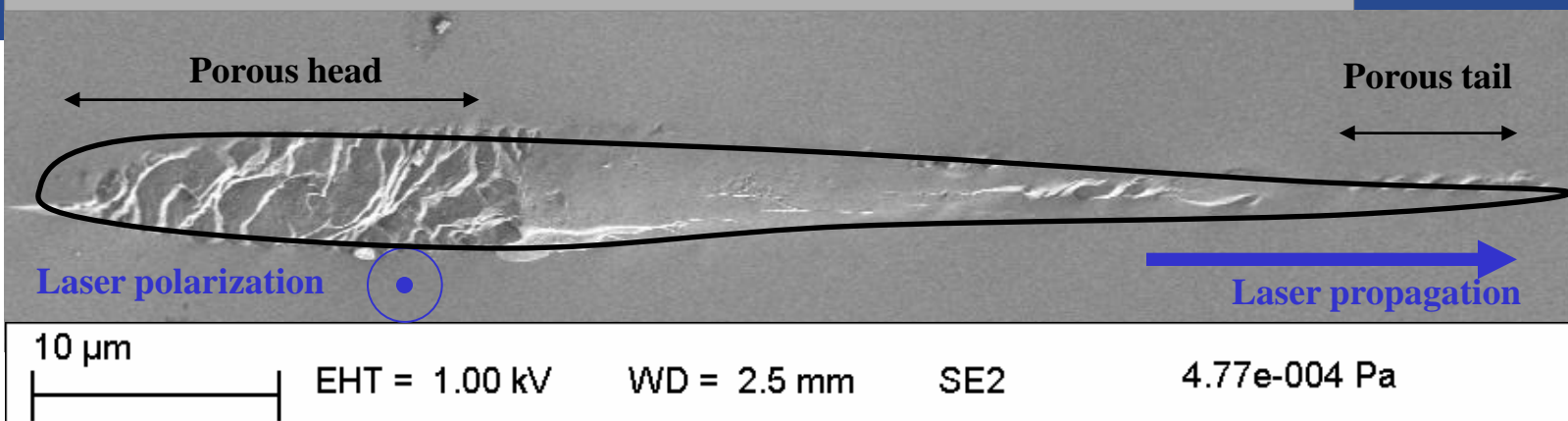
Laser track

SEM and AFM



SiO₂, 1030 nm, 250 fs, 100 kHz, 100 μm/s, 0.5 μ, 0,6 NA

SEM images of a whole laser track written in parallel configuration.

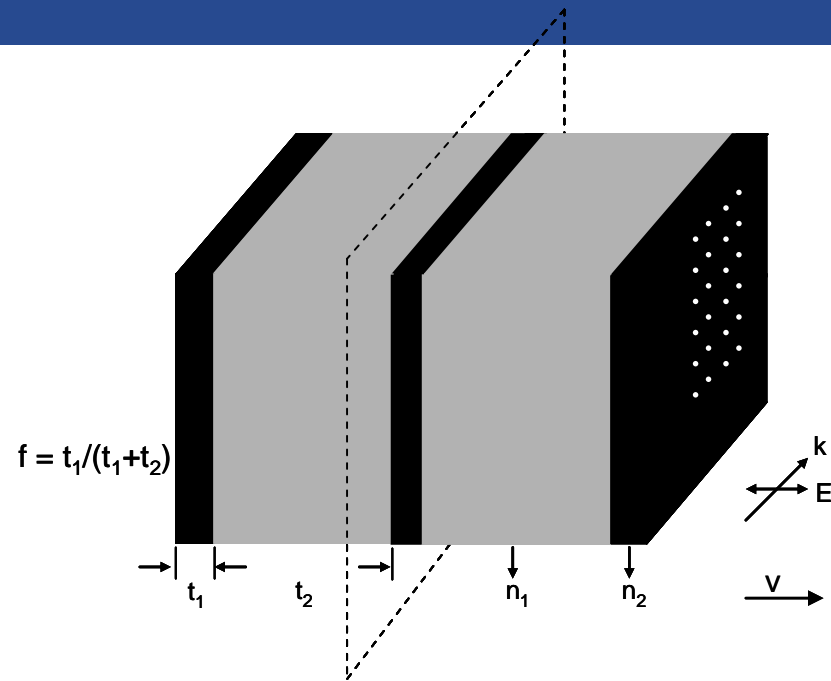


Observation repeatable over more than 200 laser tracks written with various laser parameters !!!

Decomposition of SiO_2 into $x.\text{O}_2$ + $\text{SiO}_{2(1-x)}$ initiated by 200fs photo-excitation !!!

SiO_2 , 1030 nm, 250 fs, 100 kHz, 100 $\mu\text{m/s}$, 0.5 μJ , 0,6 NA

The nanoplans produces form birefringence



Bricchi, E., B. G. Klappauf, et al. (2004). "Form birefringence and negative index change created by femtosecond direct writing in transparent materials." *Optics Letters* 29(1): 119-121.

Nanogratings filling factor (deduced from SEM observations): $f = t_1/(t_1+t_2) = 0.2$

$$\Delta n_e = \left[\sqrt{\frac{n_1^2 n_2^2}{f n_2^2 + (1-f) n_1^2}} - n_{bg} \right], \quad // \text{ writing polarization}$$

$$\Delta n_o = \left[\sqrt{f n_1^2 + (1-f) n_2^2} - n_{bg} \right]$$

material between the nanoplans unchanged i.e. pure silica $n_1=1.45$ →

Then, for a birefringence of 10^{-2} , we deduce a decrease of index by 0.2 in the nanoplanes

Large interest: birefringence is large 10^{-2} , orientable and local and extremely stable



Many possibilities for elaborating optics with unpreceding thermal resistance, but « only in pure silica » at this date.

A few words about chemical composition dependence

Lancry *et. al*, OSA, AIOM 2009, AWB4

Birefringence

Samples	IR-fs Isotropic Δn	IR-fs Birefringence	UV-ns, Isotropic Δn (\pm)
Pure SiO ₂	up to +2.2 · 10⁻²	Yes, up to 8 · 10⁻³	Up to 4 · 10⁻⁴ but very high cumulated fluence
GeO ₂ -SiO ₂ (GeO ₂ up to 20w%)	up to +10⁻² , but narrow processing window	Yes, up to 1.2 · 10⁻²	Up to 4 · 10⁻³ (H ₂ -loaded)
F-doped SiO ₂	up to +8 · 10⁻³ , wide processing window	Yes, up to 5 · 10⁻³	Up to 3 · 10⁻⁴
P-doped SiO ₂	up to +8 · 10⁻³	Yes, up to 8 · 10⁻³	Up to 4 · 10⁻³ (H ₂ -loaded)

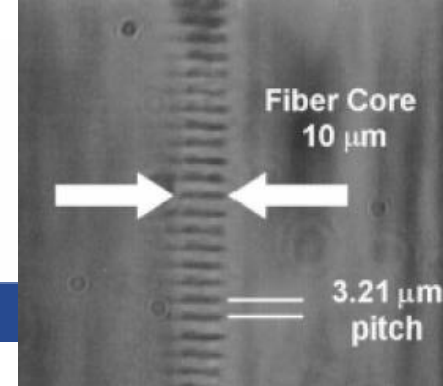
Only isotropic Δn !

SiO ₂ -SnO ₂ (16 mol%)	up to -5 · 10⁻³ , +4 · 10⁻³	No	Up to 3 · 10⁻³ but strong scattering loss
Boro-silicate (BK7)	up to +/- 10⁻²	No	A few 10⁻⁴
Lead-silicate (SF57)	up to +2 · 10⁻²	No	Up to 9 · 10⁻² but surface relief gratings
Bi ₂ O ₃ based glass	up to +5 · 10⁻³	No	?
Soda-lime	up to +3 · 10⁻³	No	A few 10⁻⁴

Femtosecond laser 3D processing in silica-based glasses

Part 3

Applications



Mihailov et al., Opt. Lett. 28 (2003)

Réseaux d'indice de réfraction:

- FBG (Fiber Bragg Gratings) stables $> 1000^{\circ} \text{ C}$
- FBG à travers le revêtement polymères
- FBG pour laser fibrés (stabilisation λ)
- Bragg en Volume pour lasers (CPA, égalisation gain)

Propriétés utilisées: fort Δn (qq 10^{-2}), biréfringence (pour maintien de polarisation), trous en volume, stabilité thermique, peu sensible à la composition chimique, localisé spatialement

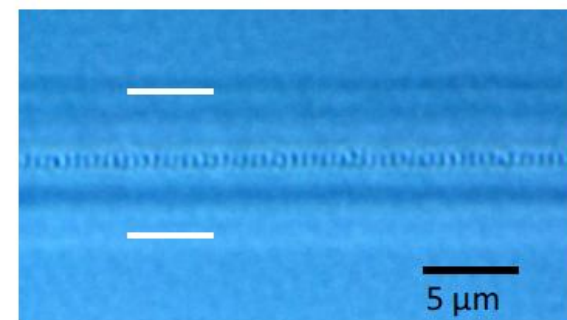
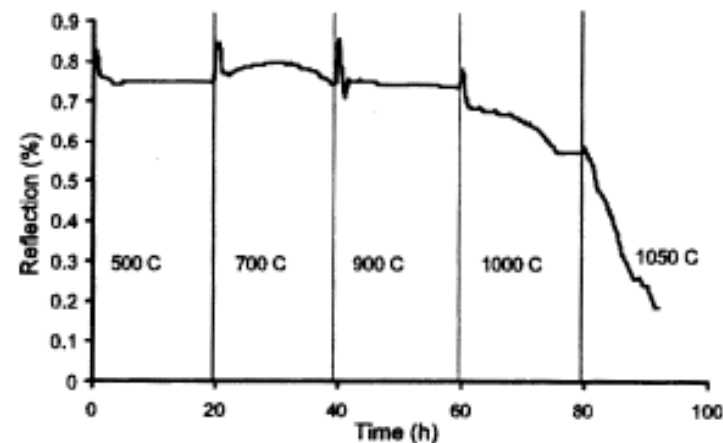


Fig. 5. Microscope image of the WBG. The small pitch of $0.52 \mu\text{m}$ can clearly be seen. The white bars mark the full width of the waveguide.

Miese et al. OME (2011)



Contrat FP7-PEOPLE-IRSES (2010-2014) en collaboration avec OFTC Sydney, UO-FSU Jena et ORC Southampton.

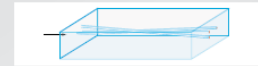
Collaborateurs industriels : Thales RT, Thales laser, 3S Photonics



Applications II

photonic devices

3D splitter



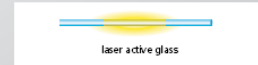
Bragg grating



demultiplexer



amplifier

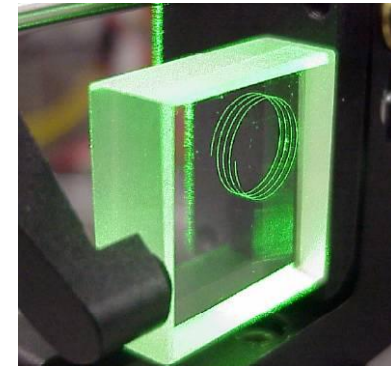


interferometer



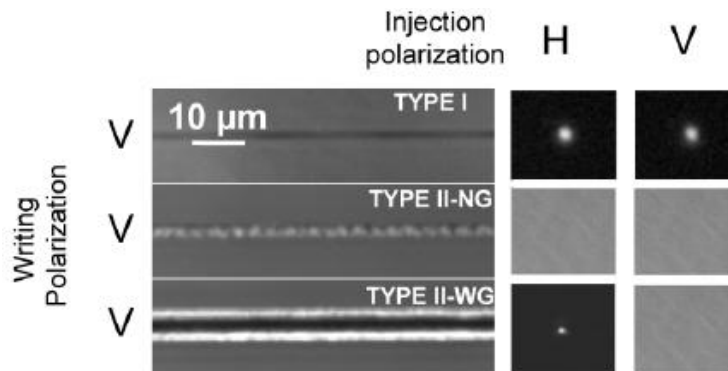
Guides optiques monomodes en 3D présentant une atténuation compatible avec les télécoms ($<0.1\text{dB/cm}$): coupleurs, séparateurs, polariseurs etc ... (puces biophotoniques, microfluidique)

Propriétés utilisées: fort Δn isotrope ($qq\ 10^{-2}$), Δn anisotrope pour guides d'onde enterré, biréfringence, stabilité thermique, localisé spatialement, vitesse élevée ($qq\text{cm/s}$).



Guide d'onde courbe
Translume compagny (USA)

Guides optiques doubleurs de fréquence



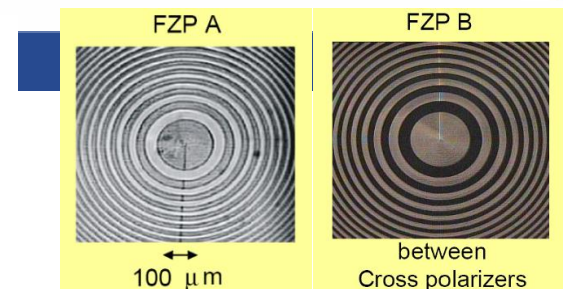
Guide d'onde (C. Mishchik PhD)

Contrat FP7-PEOPLE-IRSES (2010-2014) en collaboration avec Macquarie University and Sydney University

Composants optiques (où la biréfringence et son orientation sont maîtrisées) pour la mise en forme des faisceaux lasers et l'imagerie.

Propriétés utilisées: forte biréfringence

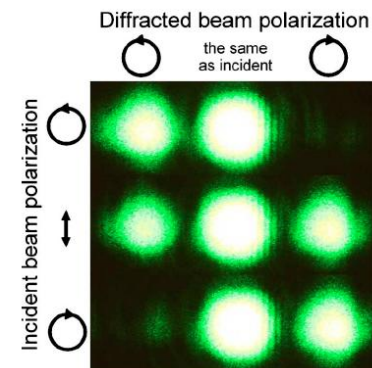
Optiques 2D/3D: lentilles de Fresnel ou lame de phase annulaires, convertisseurs de polarisation, lames d'onde UV-Vis-IR ($\lambda/4$, $\lambda/2$ et plus...), polariseurs, films compensateurs pour écrans LCD, micro-lentilles (50 μm focale), ...



Lentille de Fresnel (collab ORC southampton)



Radial or azimuthal polarization converter (collab ORC southampton)



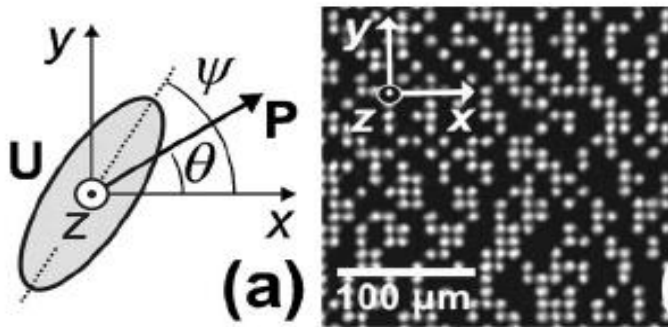
Contrat FP7-PEOPLE-IRSES (2010-2014) en collaboration avec UO-FSU Jena et ORC Southampton.

Collaborateurs industriels : Thales RT , Thales laser, Jobin Yvon

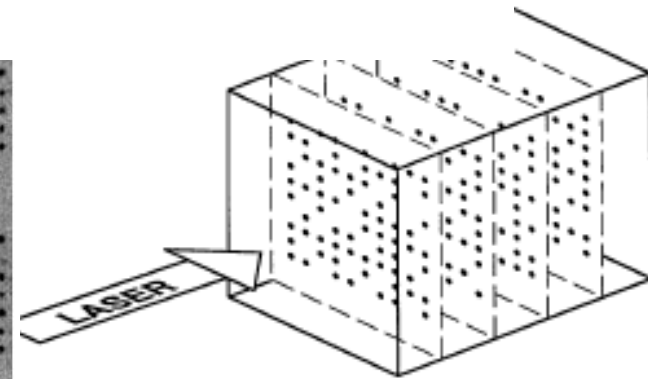
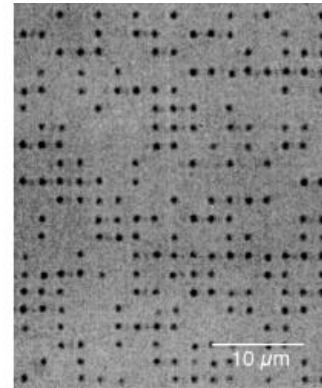
Applications IV

Stockage optique d'information en 3D

Propriétés utilisées: « fort » Δn ou la luminescence, stabilité thermique (durée de vie élevée et possibilité de faire de la prédiction !!), localisé spatialement (capacité de stockage).



Papazoglou et al., Opt. Lett. 28 (2003)



E. N. Glezer et al., Opt. Lett. 1996

Collaborations:
Gilles Pauliat
 (Institut
 d'optique), Glazt
 compagny



The different color of each letter is corresponding to the different orientation of the slow axis of the birefringence

Conclusion and perspectives

In contrast to what is observed with UV lasers, *fs Vis-IR lasers* provide a powerful tool to direct-write *strong permanent (isotropic AND anisotropic) Δn up to 10^{-2}* in “*any glasses*”, without the need for any photosensitization process and *with superior thermal stability (up to 1000°C) !!!*

Ultrafast Vis-IR laser also has one substantial advantage over UV lasers – the *internal structuring of 3D index profiles* in transparent glasses. This presents interesting prospects for shaping 3D photonic structures for optical telecommunication, high power laser, optical data storage, LCD, sensors, ...

Ultrafast Vis-IR laser implies a *slower processing* (to overcome using high power 100's kHz and 10's MHz laser), but one that *offers more flexibility* in patterning and trimming applications.

But also :form birefringence, nanostructures, linear dichroism, circular dichroism, metallic nanoparticles precipitation and shaping, nano/micro-crystallization and so more ...



Acknowledgements to *FLAG* consortium



UPS/ICMMO, UPS/ISMO, CEA/LSI-IRAMIS, UVSQ/LISV, UB1/CPMOH, THALES RT
iPL/USyd, MQ, ORC Southampton/UK, Friedrich-Schiller-Uni/Jena

Femtosecond Laser for Applications in Glasses

Supported by

FP7-PEOPLE-IRSES

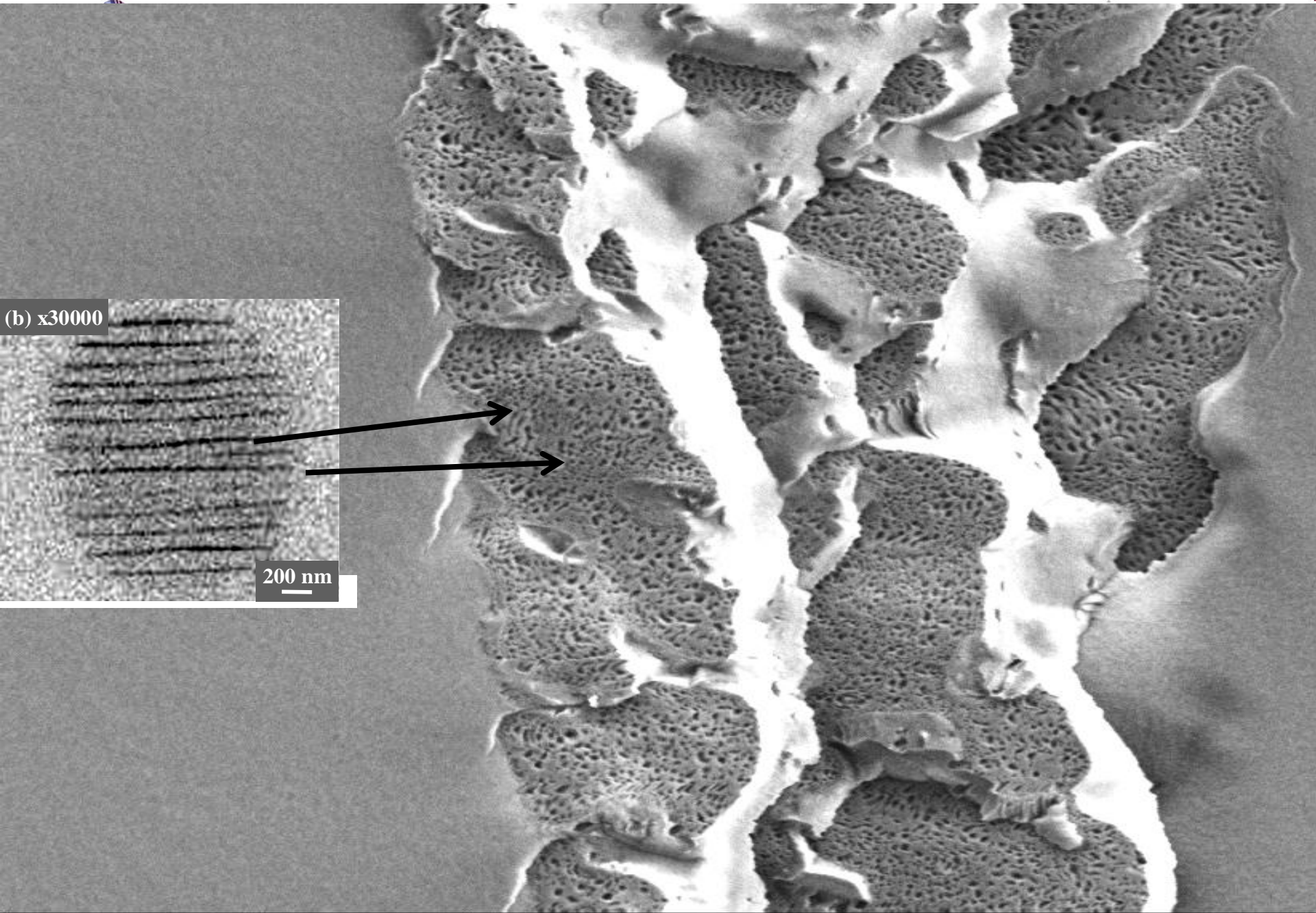
Agence Nationale pour la Recherche

RTRA Triangle de la Physique

Département de l'Essonne



The different colors of each letter correspond to different orientations of the slow axis of the birefringence (due to different nanograting orientation).



(b) x30000

200 nm

1 μm

EHT = 1.00 kV

WD = 1.9 mm

SE2